MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating		Symbol	Value	Unit
Off-State Voltage - Maximum	MMT10B230T3 MMT10B260T3 MMT10B310T3	V _{DM}	±170 ±200 ±270	V
Maximum Pulse Surge Short Circuit Current Non–Repetitive Double Exponential Decay Waveform (Notes 1 and 2) (–20°C to +65°C) 2 x 10 μsec 10 x 700 μsec 10 x 1000 μsec		IPPS1 IPPS2 IPPS3	±500 ±180 ±100	A(pk)
Maximum Non–Repetitive Rate of Change of On–State Current Double Exponential Waveform, $R=2.0,L=1.5\;\mu\text{H},C=1.67\;\mu\text{F},\\ I_{pk}=110\text{A}$		di/dt	±100	A/μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. Allow cooling before testing second polarity.
- 2. Measured under pulse conditions to reduce heating.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Operating Temperature Range Blocking or Conducting State	T _{J1}	-40 to +125	°C
Overload Junction Temperature – Maximum Conducting State Only	T _{J2}	+175	°C
Instantaneous Peak Power Dissipation (I _{pk} = 100 A, 10x1000 μsec @ 25°C)		4000	W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ORDERING INFORMATION

Device	Package	Shipping [†]
MMT10B230T3	SMB	
MMT10B230T3G	SMB (Pb-Free)	
MMT10B260T3	SMB	(12mm) Tana & Baal
MMT10B260T3G	SMB (Pb-Free)	(12mm) Tape & Reel 2500 Units per Reel
MMT10B310T3	SMB	
MMT10B310T3G	SMB (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

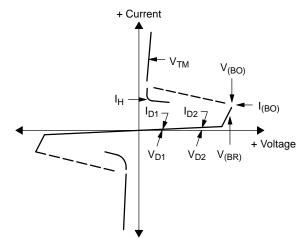
Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

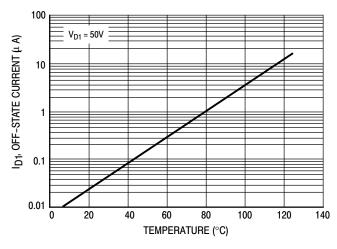
Characteristic		Symbol	Min	Тур	Max	Unit
Breakover Voltage (Both polarities) (dv/dt = 100 V/μs, I _{SC} = 1.0 A, Vdc = 1000 V)	MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G	V _(BO)	- - -	- - -	265 320 365	V
(+65°C)	MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G		- - -	- - -	290 340 400	
Breakover Voltage (Both polarities) $ (f=60~Hz,~I_{SC}=1.0~A(rms),~V_{OC}=1000~V(rms), \\ R_{I}=1.0~k\Omega,~t=0.5~cycle)~(Note~3) $ $ (+65^{\circ}C) $	MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G	V _(BO)	-		265 320 365 290 340 400	V
Breakover Voltage Temperature Coefficient		dV _(BO) /dT _J	_	0.08	_	%/°C
Breakdown Voltage ($I_{(BR)} = 1.0 \text{ mA}$) Both polarities	MMT10B230T3, G MMT10B260T3, G MMT10B310T3, G	V _(BR)	- - -	190 240 280	- - -	V
Off State Current ($V_{D1} = 50 \text{ V}$) Both polarities ($V_{D2} = V_{DM}$) Both polarities		I _{D1} I _{D2}	-	_ _	2.0 5.0	μΑ
On–State Voltage (I_T = 1.0 A) (PW \leq 300 μ s, Duty Cycle \leq 2%) (Note 3)		V _T	_	1.53	5.0	V
Breakover Current (f = 60 Hz, V _{DM} = 1000 V(rms), I Both polarities	R _S = 1.0 kΩ)	I _{BO}	_	260	-	mA
Holding Current (Both polarities) $V_S = 500 \text{ Volts}; I_T \text{ (Initiating Current)} = \pm 1.0 \text{ A}$	(Note 3)	I _H	150	270	-	mA
Critical Rate of Rise of Off–State Voltage (Linear waveform, V_D = Rated V_{BR} , T_J = 25°C)		dv/dt	2000	-	-	V/µs
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signa (f = 1.0 MHz, 2.0 Vdc, 15 mV rms Sign	,	Co	- -	65 160	- 200	pF

^{3.} Measured under pulse conditions to reduce heating.

Voltage Current Characteristic of TSPD (Bidirectional Device)

Symbol	Parameter
I _{D1} , I _{D2}	Off State Leakage Current
V_{D1}, V_{D2}	Off State Blocking Voltage
V_{BR}	Breakdown Voltage
V _{BO}	Breakover Voltage
I _{BO}	Breakover Current
I _H	Holding Current
V_{TM}	On State Voltage

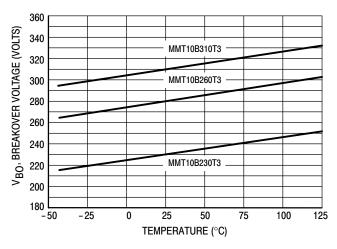




340 V_{BR}, BREAKDOWN VOLTAGE (VOLTS) 320 MMT10B310T3 300 280 260 MMT10B260T3 240 220 200 MMT10B230T3 180 160 50 25 100 125 -50 TEMPERATURE (°C)

Figure 1. Off-State Current versus Temperature

Figure 2. Breakdown Voltage versus Temperature



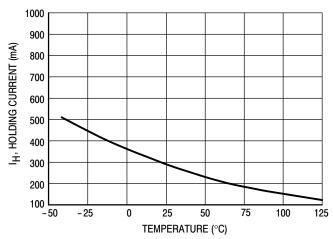
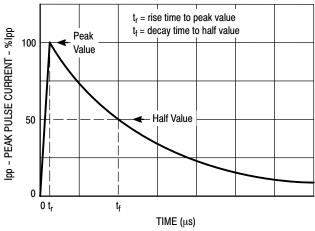


Figure 3. Breakover Voltage versus Temperature

Figure 4. Holding Current versus Temperature





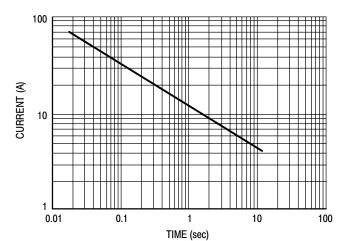
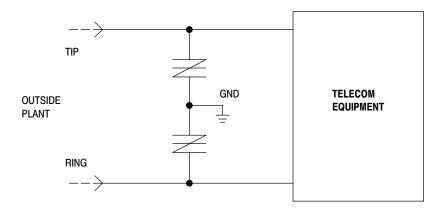
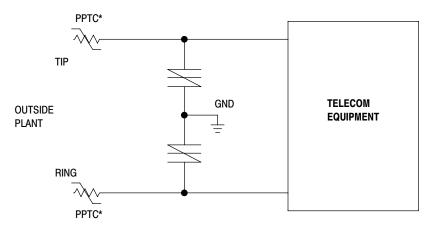
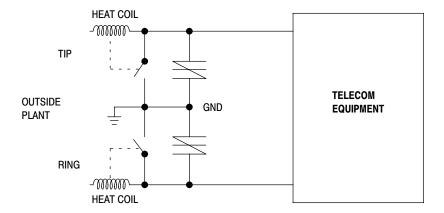


Figure 6. Peak Surge On-State Current versus Surge Current Duration, Sinusoidal Waveform





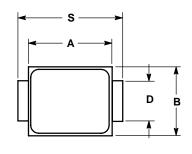
*Polymeric PTC (positive temperature coefficient) overcurrent protection device

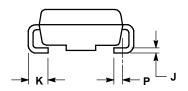


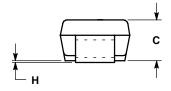
PACKAGE DIMENSIONS

SMB

(No Polarity) (Essentially JEDEC DO-214AA) CASE 403C-01 ISSUE A



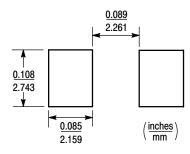




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.160	0.180	4.06	4.57
В	0.130	0.150	3.30	3.81
С	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
Н	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
K	0.030	0.050	0.76	1.27
Р	0.020	0.020 REF 0.51 REF		REF
S	0.205	0.220	5.21	5.59

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D

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